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Université Abou Bekr Belkaid
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titre:

*A coparative study between B GaN layers grown on
GaN/Al₂O₃ and AlN/Al₂O₃ by MOVPE*

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Résumé :

III-nitride wide band gap semiconductors (GaN, AlN, and InN) have recently attracted considerable interest

Mots clefs :

B GaN, GaN/ Al₂O₃, AlN/Al₂O₃, SEM, AFM, XRD,MOVPE

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